



YJS12G06D

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	60V
I_D	12A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	8.5 mohm
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	12 mohm
100% EAS Tested	

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Typical Performance Characteristics

Figure1. Output Characteristics



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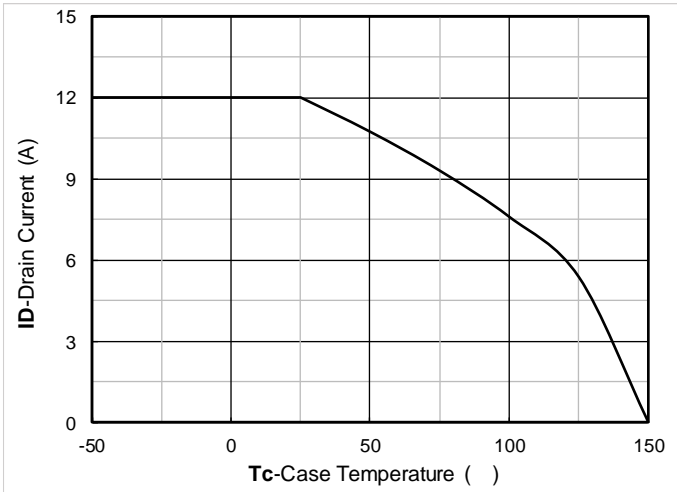


Figure7. Drain current

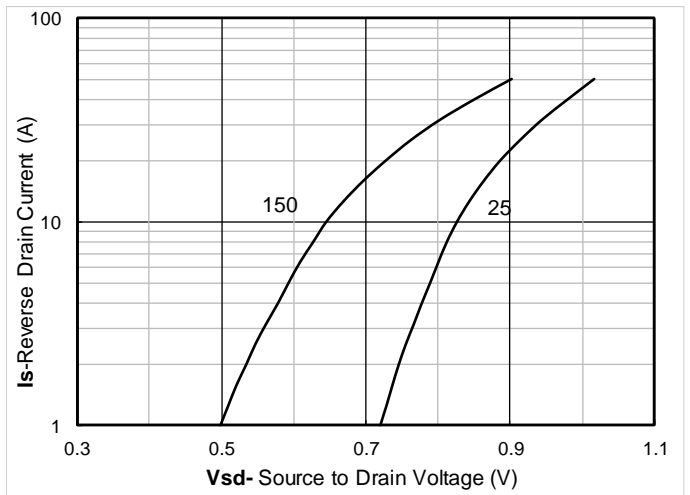


Figure8. Safe Operation Area

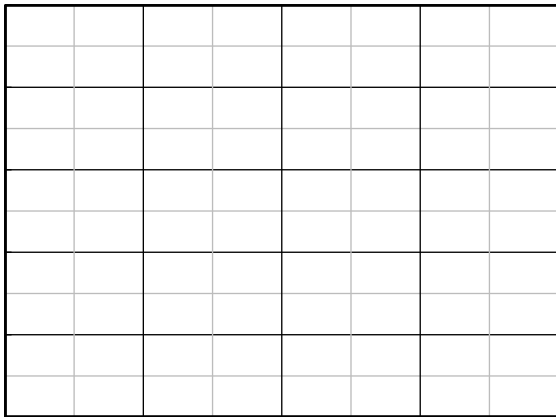


Figure 9. On-Resistance vs Gate to Source Voltage

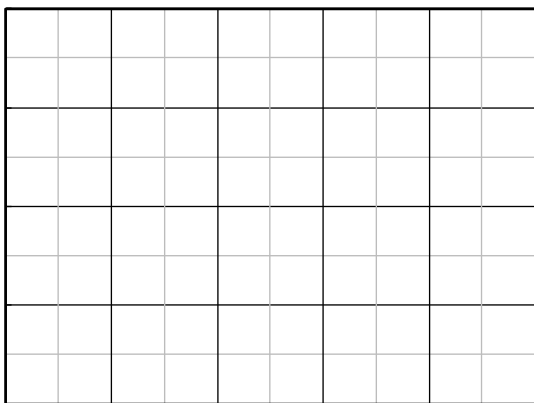


Figure 11. Normalized breakdown voltage

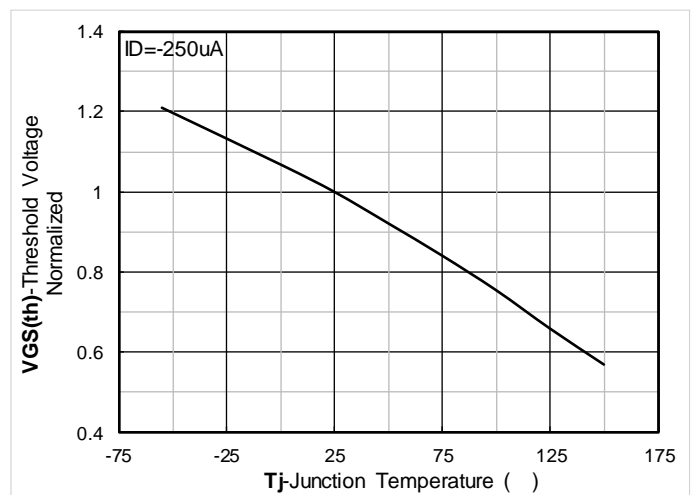


Figure 1



Figure

